

3DD171(172), 3DD175(176)**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					
			3DD171			3DD175		
			A	B	C	D	E	F
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300
C-Base Breakdown Voltage	$V_{(BR)CBO}$	V	3DD171: $I_C=5mA$			3DD175: $I_C=5mA$		
			80	150	200	250	350	400
Emitter-Base Voltage	V_{EBO}	V	5			5		
Max. Collector Current	I_{CM}	A	20			30		
Max. Collector Dissipation	P_{CM}	W	200 ($T_c \leq 75^\circ C$)			300 ($T_c \leq 75^\circ C$)		
Junction Temperature	T_{jm}	$^\circ C$	175					
Storage Temperature	T_{stg}	$^\circ C$	-55~+175					
Collector-Emitter Leakage Current	I_{CEO}	mA	3.0 (A: $V_{CE}=30V$;B: $V_{CE}=50V$; C~F: $V_{CE}=100V$)					
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.8 ($I_C=10A, I_B=1A$)			2.0 ($I_C=15A, I_B=1.5A$)		
DC Current Gain	h_{FE}		Max.:180,Min.:15 ($V_{CE}=5V, I_C=10A$)			Max.:180, Min.:15 ($V_{CE}=5V, I_C=15A$)		
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 ($I_E=15mA$)			≥ 5 ($I_E=15mA$)		

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: